

Conventional memory technologies : Flash memory

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- Current technology
- Scaling roadmap
- issues and potential roadblocks.
- Including 3D Flash

Youngwoo Park

Dr. Youngwoo Park is a Master in semiconductor R&D center at Samsung Electronics. He joined Samsung Electronics in 1987 and he developed DRAM from 1987 to 1999.

He received his Ph. D in electrical engineering from University of California, Los Angeles in 2005. Since 2005, he has been developing NAND Flash devices including planar NAND Flash and 3D Vertical NAND Flash. He became a Master of Samsung Electronics in 2009. His current research area is developing the advanced NAND Flash devices.

He received the Samsung Award of Honor in 1994 and in 2007, respectively, and the Patent Award from Minister of Commerce, Industry and Energy in 2000. He holds 125 US patents and 45 papers.